M54HC151 M74HC151

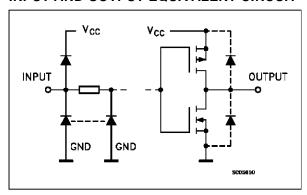
8 CHANNEL MULTIPLEXER

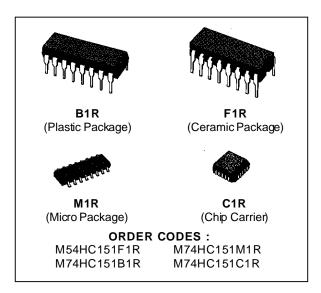
- HIGH SPEED
 - $t_{PD} = 15 \text{ ns} (TYP.) AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 4 \mu A \text{ (MAX.)} \text{ AT } T_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | IOH | = IoL = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS151

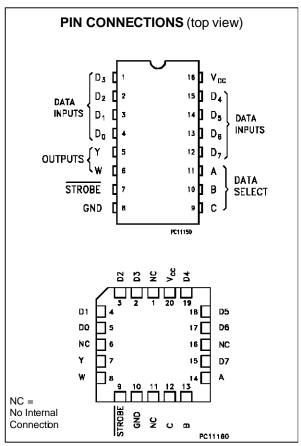
DESCRIPTION

The M54/74HC151 is a high speed CMOS 8 CHANNEL MULTIPLEXER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It provides, in one package, the ability to select one bit of data from up to eight sources. The HC151 can be used as a universal function generator to generate any logic function of four variables. Outputs Y and W are complementary selection depends on the address inputs A, B and C. The strobe input must be taken low to enable this device, when the strobe is high W output is forced high and consequently Y output goes low. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







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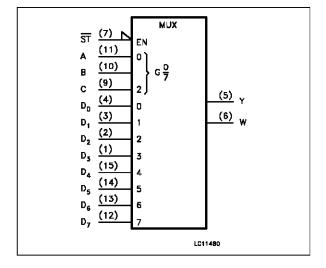
TRUTH TABLE

	INP	OUTPUTS			
	SELECT		STROBE		w
С	В	Α	s	ı	VV
Х	X	X	Н	L	Н
L	L	L	L	D0	D0
L	L	Н	L	D1	D1
L	Н	L	L	D2	D2
L	Н	Н	L	D3	D3
Н	L	L	L	D4	D4
Н	L	Н	L	D5	D5
Н	Н	L	L	D6	D6
Н	Н	Н	L	D7	D7

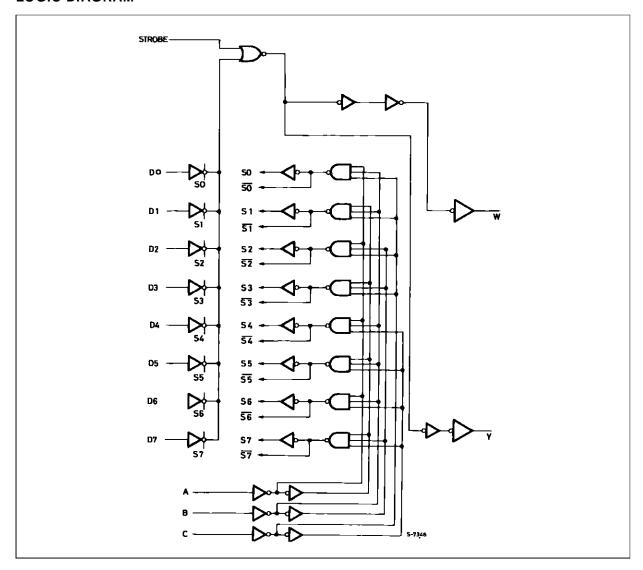
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
4, 3, 2, 1, 15, 14, 13,	D0 to D7	Multiplexer Inputs
12		
5	У	Multiplexer Output
6	w	Complementary
		Multiplexer Output
7	STROBE	Strobe Input
11, 10, 9	A, B, C	Select Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
V_{I}	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
l _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
lο	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \equiv 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
Vcc	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
Тор	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 2 V$	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		V _{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

		Test Conditions		Value								
Symbol	Parameter	V _{CC}			T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V_{OH}	High Level	2.0	V _I =	Ι _Ο =-20 μΑ	1.9	2.0		1.9		1.9		.,,
	Output Voltage	4.5	VI –		4.4	4.5		4.4		4.4		
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI =	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
	4.5	V _{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.40		
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	√cc or GND			4		40		80	μΑ

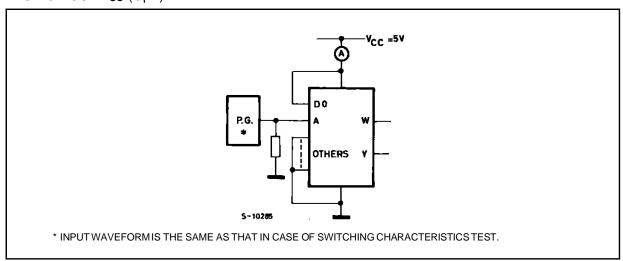


AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

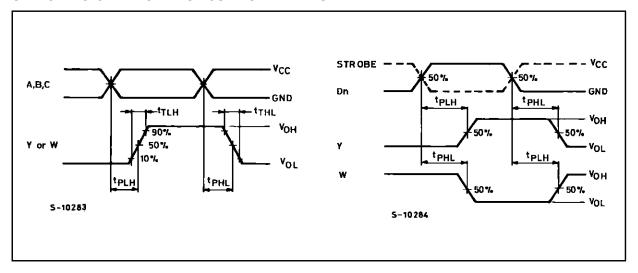
		Test Conditions		Value						
Symbol	Symbol Parameter	Vcc	T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0		30	75		95		110	
t _{THL}	Time	4.5		8	15		19		22	ns
		6.0		7	13		16		19	
t _{PLH}	Propagation	2.0		56	130		165		190	
t _{PHL}	Delay Time	4.5		16	26		33		38	ns
	(D - W)	6.0		14	22		28		32	
t _{PLH}	Propagation	2.0		56	130		165		190	
t _{PHL}	Delay Time	4.5		16	26		33		38	ns
	(D - Y)	6.0		14	22		28		32	
t _{PLH}	Propagation	2.0		30	85		105		125	ns
t _{PHL}	Delay Time	4.5		10	17		21		25	
	(STROBE - W)	6.0		9	14		18		21	
t _{PLH}	Propagation	2.0		30	85		105		125	
t _{PHL}	Delay Time	4.5		10	17		21		25	ns
	(STROBE - Y)	6.0		9	14		18		21	
t _{PLH}	Propagation	2.0		72	160		200		235	
t _{PHL}	Delay Time	4.5		20	32		40		47	ns
	(A, B, C - W)	6.0		17	27		34		40	
t _{PLH}	Propagation	2.0		72	160		200		235	
t _{PHL}	Delay Time	4.5		20	32		40		47	ns
	(A, B, C - Y)	6.0		17	27		34		40	
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			63						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. I_{CC}(opr) = C_{PD} • V_{CC} • f_{IN} + I_{CC}

TEST CIRCUIT Icc (Opr.)

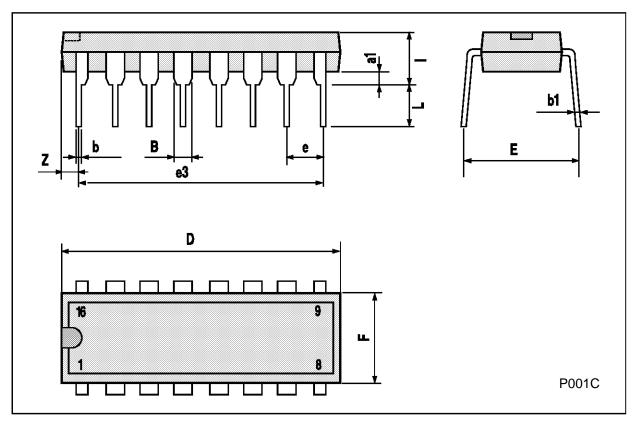


SWITCHING CHARACTERISTICS TEST WAVEFORM



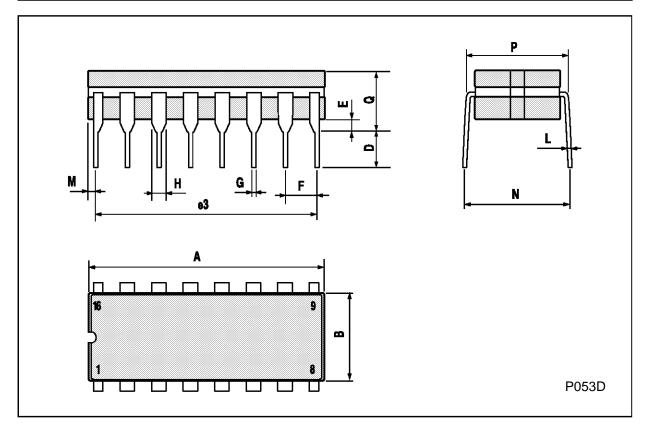
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z			1.27			0.050	



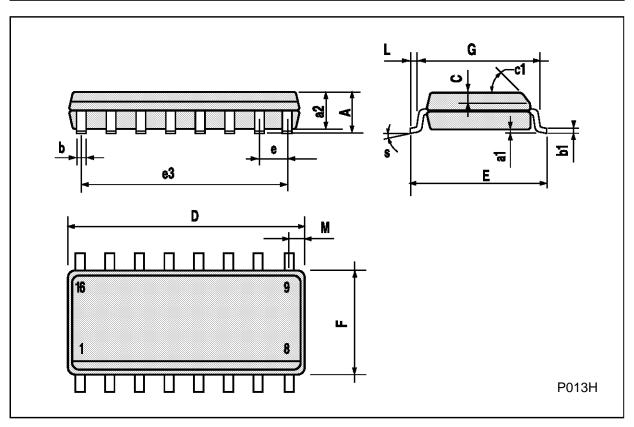
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			20			0.787	
В			7			0.276	
D		3.3			0.130		
Е	0.38			0.015			
e3		17.78			0.700		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
М	0.51		1.27	0.020		0.050	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



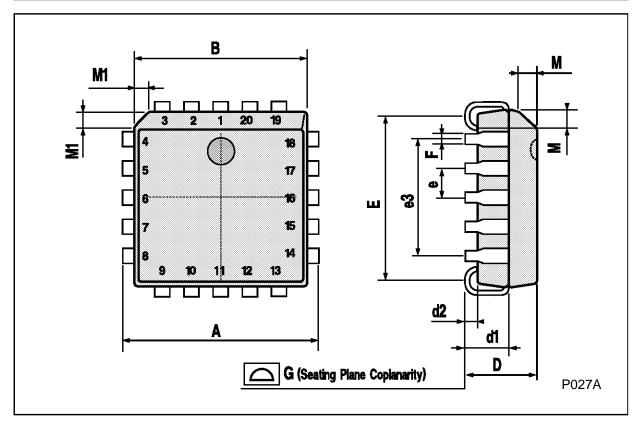
SO16 (Narrow) MECHANICAL DATA

DIM.		mm				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	9.8		10	0.385		0.393
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (ı	max.)		



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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